DATA SHEET

NEC

PHOTOCOUPLER

PS2501-1,-2,-4, PS2501L-1,-2,-4

HIGH ISOLATION VOLTAGE SINGLE TRANSISTOR TYPE MULTI PHOTOCOUPLER SERIES

–NEPOC™ Series–

DESCRIPTION

The PS2501-1, -2, -4 and PS2501L-1, -2, -4 are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon phototransistor.

The PS2501-1, -2, -4 are in a plastic DIP (Dual In-line Package) and the PS2501L-1, -2, -4 are lead bending type (Gull-wing) for surface mount.

FEATURES

- High isolation voltage (BV = 5 000 Vr.m.s.)
- High collector to emitter voltage (V_{CEO} = 80 V)
- High-speed switching (t_r = 3 μs TYP., t_f = 5 μs TYP.)
- Ordering number of taping product: PS2501L-1-E3, E4, F3, F4, PS2501L-2-E3, E4
- UL approved: File No. E72422 (S)

APPLICATIONS

- Power supply
- Telephone/FAX.
- FA/OA equipment
- Programmable logic controller

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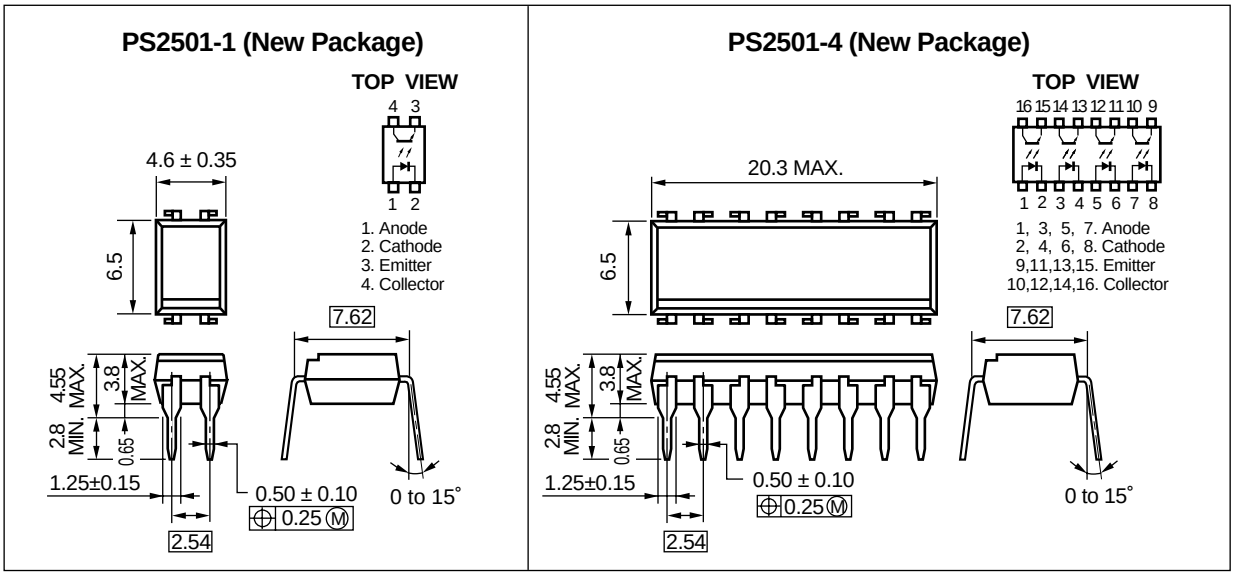
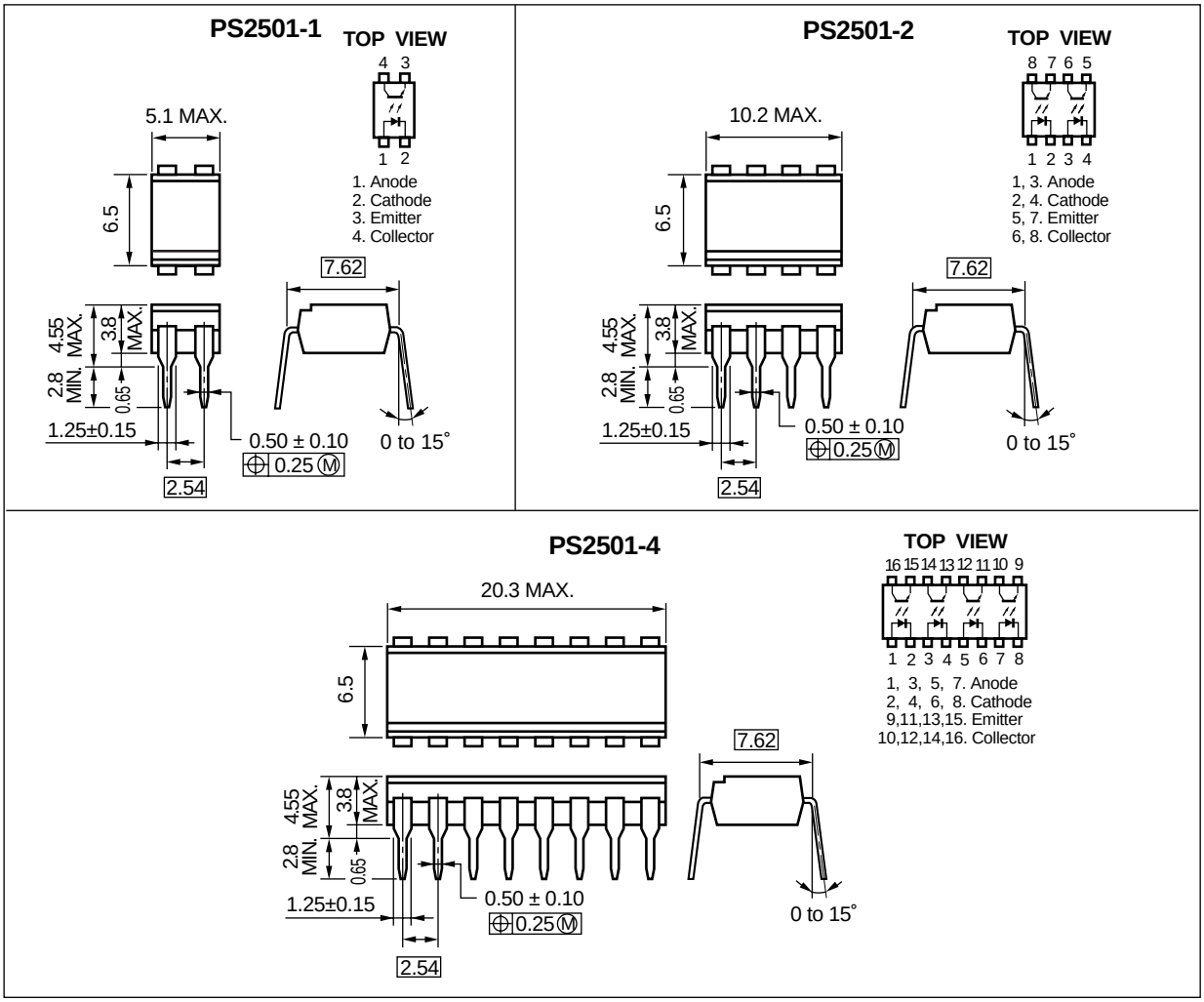
The mark ★ shows major revised points.

★ **PACKAGE DIMENSIONS (in millimeters)**

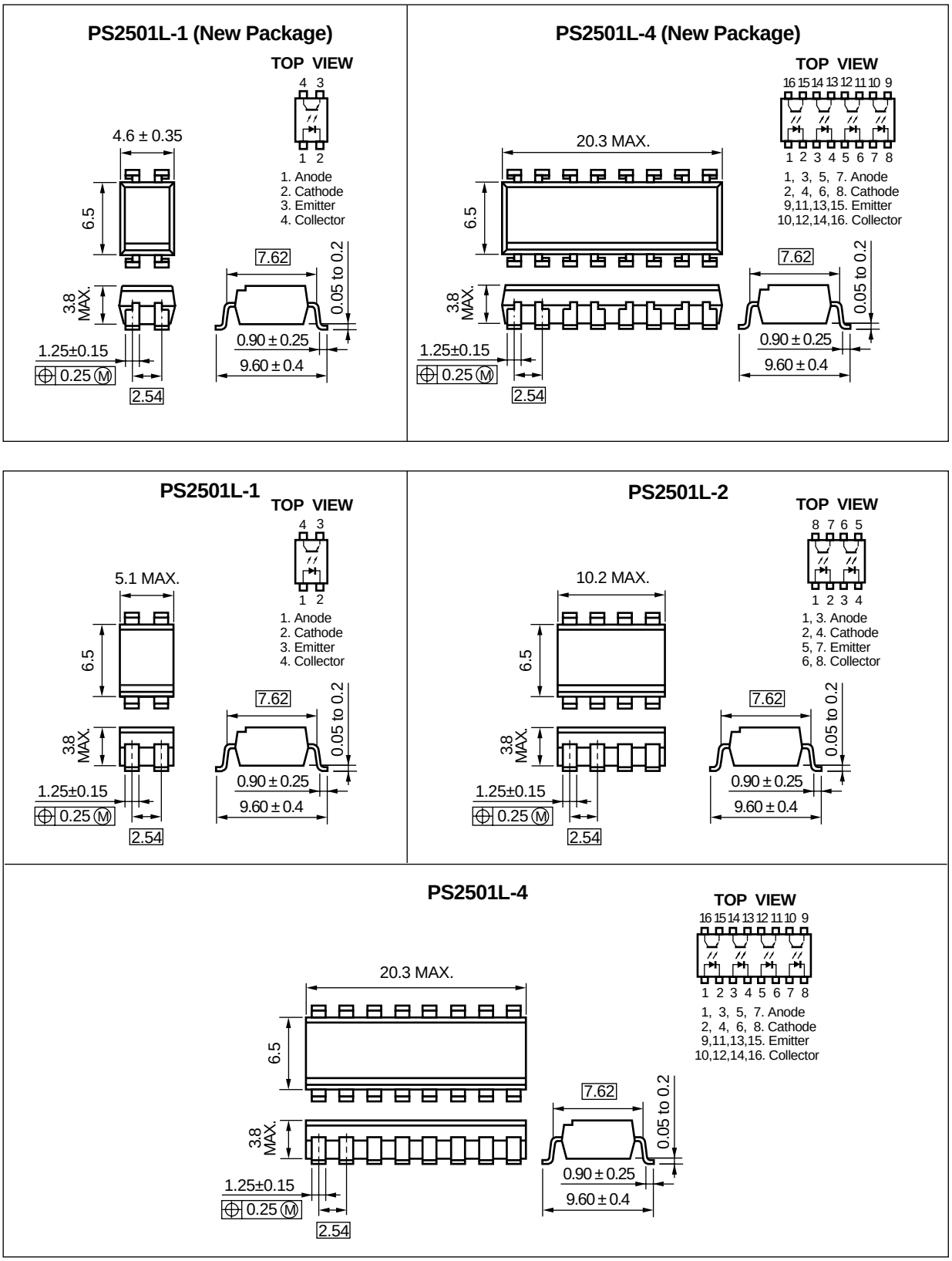
DIP Type





Caution New package 1-ch, 4-ch only

Lead Bending Type



Caution New package 1-ch, 4-ch only

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise specified)

Parameter		Symbol	Ratings		Unit
			PS2501-1, PS2501L-1	PS2501-2,-4 PS2501L-2,-4	
Diode	Reverse Voltage	V_R	6		V
	Forward Current (DC)	I_F	80		mA
	Power Dissipation Derating	ΔP_D/°C	1.5	1.2	mW/°C
	Power Dissipation	P_D	150	120	mW/ch
	Peak Forward Current*1	I_{FP}	1		A
Transistor	Collector to Emitter Voltage	V_{CEO}	80		V
	Emitter to Collector Voltage	V_{ECO}	7		V
	Collector Current	I_C	50		mA/ch
	Power Dissipation Derating	ΔP_C/°C	1.5	1.2	mW/°C
	Power Dissipation	P_C	150	120	mW/ch
Isolation Voltage*2		BV	5 000		Vr.m.s.
Operating Ambient Temperature		T_A	–55 to +100		°C
Storage Temperature		T_{stg}	–55 to +150		°C

***1** PW = 100 μs, Duty Cycle = 1 %

***2** AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output

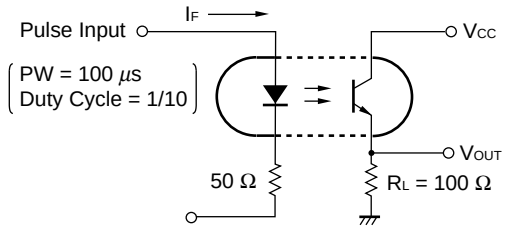
ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	V_F	I_F = 10 mA		1.17	1.4	V
	Reverse Current	I_R	V_R = 5 V			5	μA
	Terminal Capacitance	C_t	V = 0 V, f = 1.0 MHz		50		pF
Transistor	Collector to Emitter Dark Current	I_{CEO}	V_{CE} = 80 V, I_F = 0 mA			100	nA
Coupled	Current Transfer Ratio (I_C/I_F) *1	CTR	I_F = 5 mA, V_{CE} = 5 V	80	300	600	%
	Collector Saturation Voltage	$V_{CE (sat)}$	I_F = 10 mA, I_C = 2 mA			0.3	V
	Isolation Resistance	R_{I-O}	V_{I-O} = 1.0 kV_{DC}	10^{11}			Ω
	Isolation Capacitance	C_{I-O}	V = 0 V, f = 1.0 MHz		0.5		pF
	Rise Time *2	t_r	V_{CC} = 10 V, I_C = 2 mA, R_L = 100 Ω		3		μs
	Fall Time *2	t_f			5		

***1** CTR rank (* : only PS2501-1, PS2501L-1)

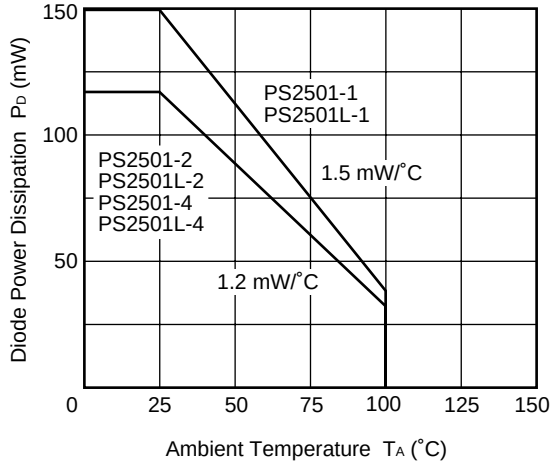
- K* : 300 to 600 (%)
- L* : 200 to 400 (%)
- M* : 80 to 240 (%)
- D* : 100 to 300 (%)
- H* : 80 to 160 (%)
- W* : 130 to 260 (%)
- Q* : 100 to 200 (%)
- ★ N : 80 to 600 (%)

***2** Test circuit for switching time

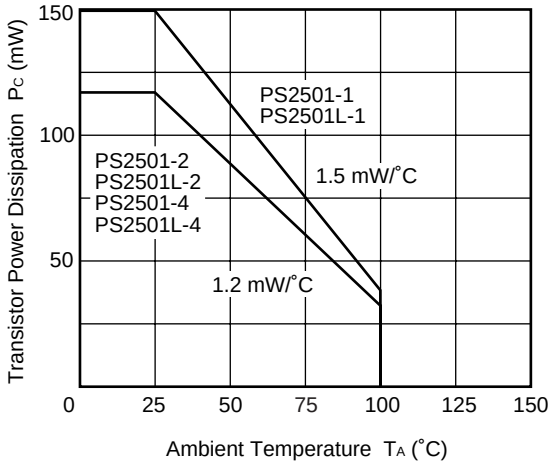


★ **TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise specified)**

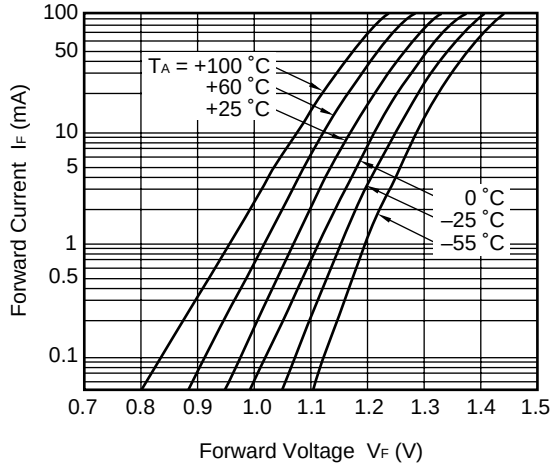
DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE



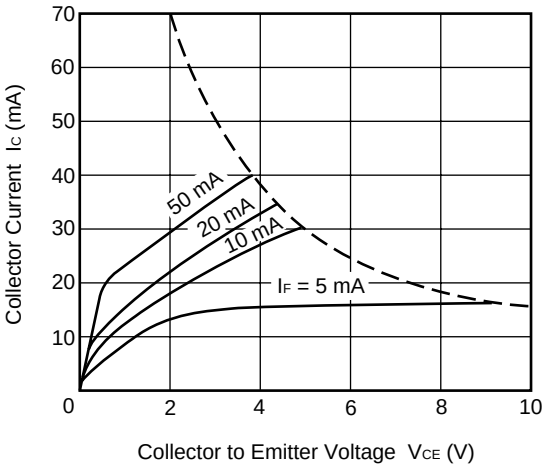
TRANSISTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE



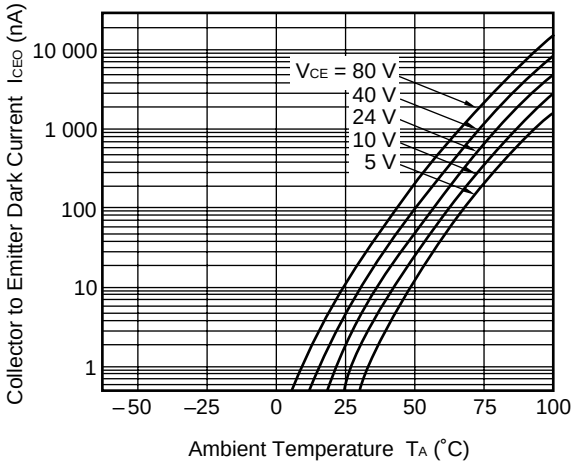
FORWARD CURRENT vs. FORWARD VOLTAGE



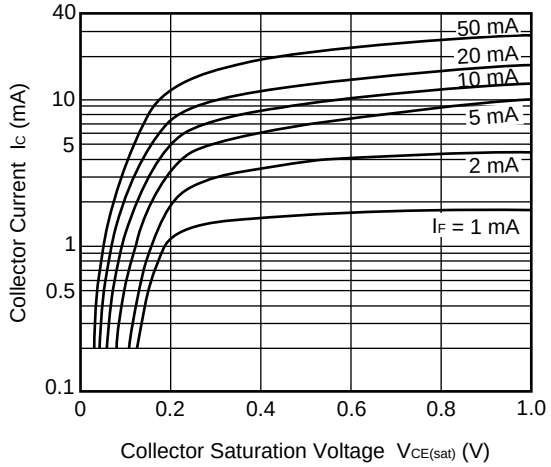
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



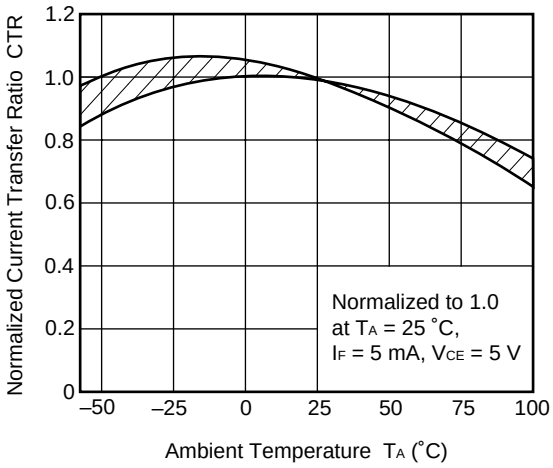
COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE



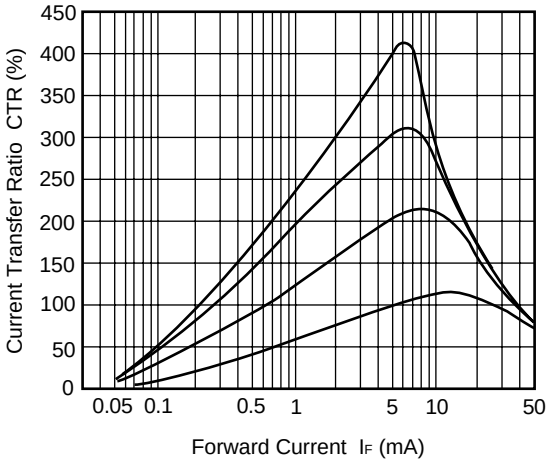
COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



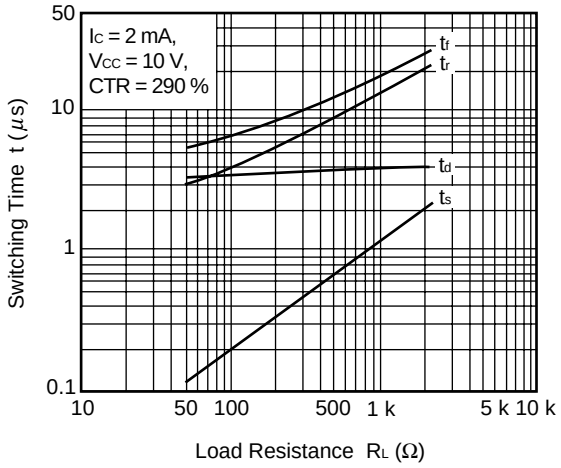
NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE



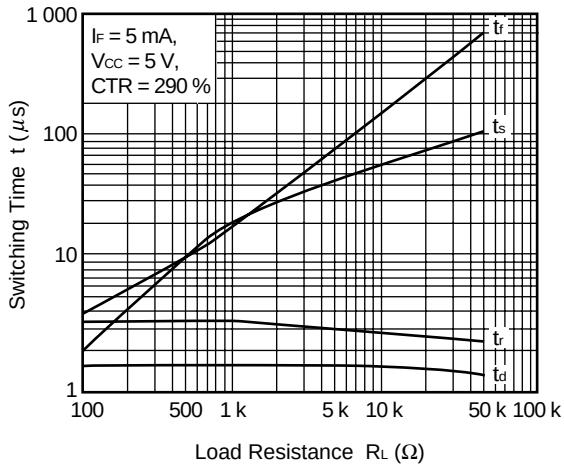
CURRENT TRANSFER RATIO vs. FORWARD CURRENT



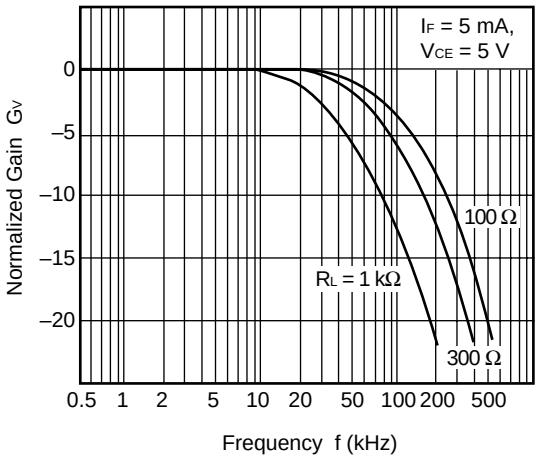
SWITCHING TIME vs. LOAD RESISTANCE



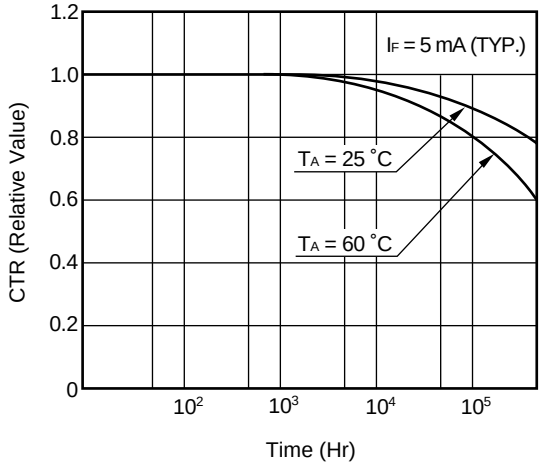
SWITCHING TIME vs. LOAD RESISTANCE



FREQUENCY RESPONSE



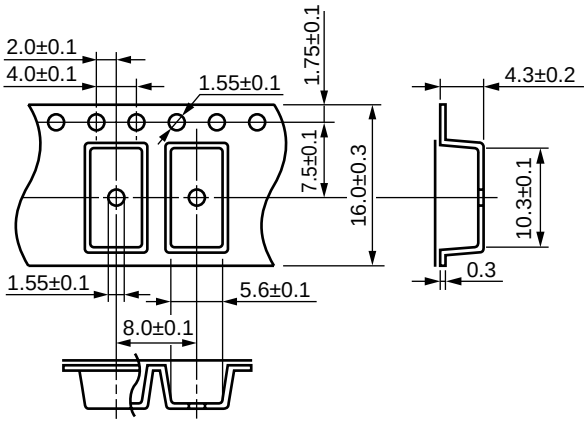
LONG TERM CTR DEGRADATION



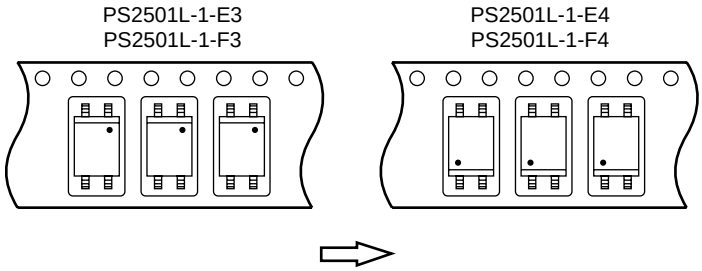
Remark The graphs indicate nominal characteristics.

★ **TAPING SPECIFICATIONS (in millimeters)**

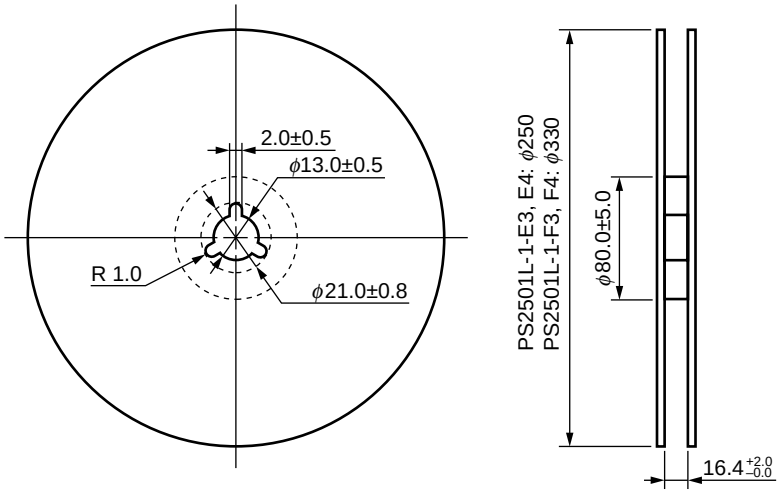
Outline and Dimensions (Tape)



Tape Direction

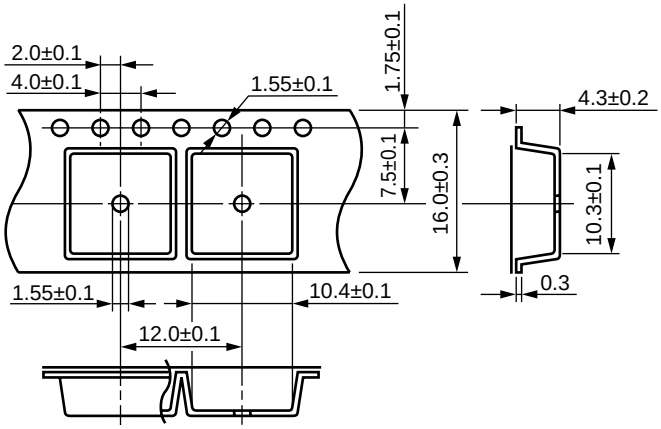


Outline and Dimensions (Reel)

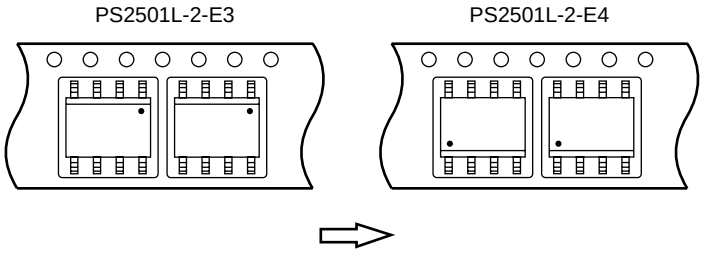


Packing: PS2501L-1-E3, E4 1 000 pcs/reel
PS2501L-1-F3, F4 2 000 pcs/reel

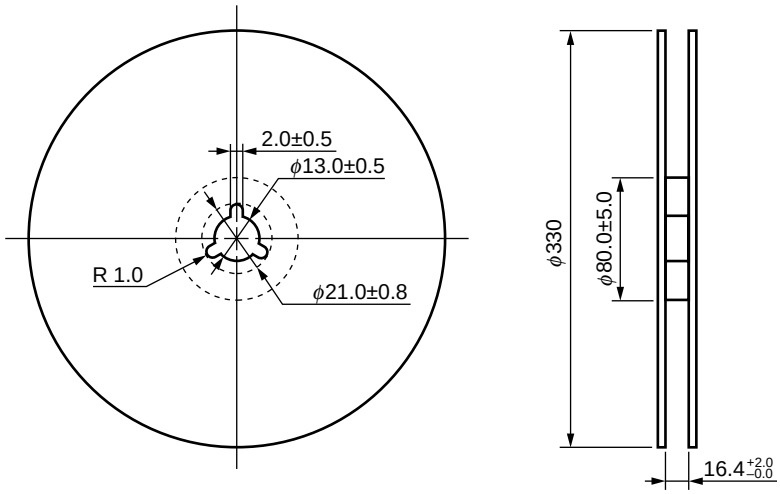
Outline and Dimensions (Tape)



Tape Direction



Outline and Dimensions (Reel)



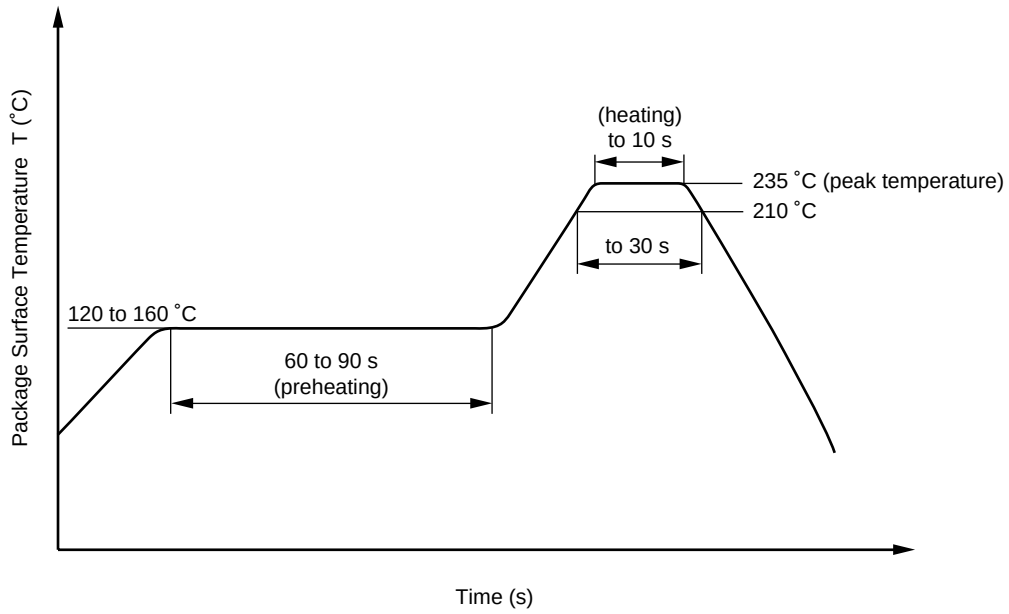
Packing: 1 000 pcs/reel

★ RECOMMENDED SOLDERING CONDITIONS

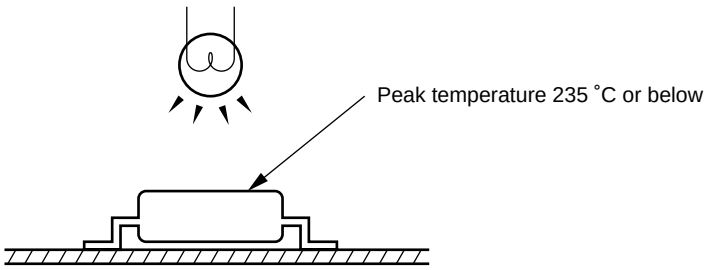
(1) Infrared reflow soldering

- Peak reflow temperature — 235 °C (package surface temperature)
- Time of temperature higher than 210 °C — 30 seconds or less
- Number of reflows — Three
- Flux — Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

Recommended Temperature Profile of Infrared Reflow



Caution Avoid removing the residual flux with chlorine-based cleaning solvent after a reflow process.



(2) Dip soldering

- Temperature — 260 °C or below (molten solder temperature)
- Time — 10 seconds or less
- Number of times — One
- Flux — Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

[MEMO]

CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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